

# Shixiong Liang

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9257697/publications.pdf>

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18  
papers

1,070  
citations

623574

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h-index

839398

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g-index

19  
all docs

19  
docs citations

19  
times ranked

976  
citing authors

#	ARTICLE	IF	CITATIONS
1	Gbps Terahertz External Modulator Based on a Composite Metamaterial with a Double-Channel Heterostructure. Nano Letters, 2015, 15, 3501-3506.	4.5	180
2	Dynamic Photoinduced Controlling of the Large Phase Shift of Terahertz Waves via Vanadium Dioxide Coupling Nanostructures. ACS Photonics, 2018, 5, 3040-3050.	3.2	111
3	Lateral $\text{In}^2\text{-Ga}_{2\text{O}_3}$ MOSFETs With High Power Figure of Merit of 277 MW/cm <sup>2</sup> . IEEE Electron Device Letters, 2020, 41, 537-540.	2.2	89
4	Demonstration of $\text{In}^2\text{-Ga}_{2\text{O}_3}$ Junction Barrier Schottky Diodes With a Baliga's Figure of Merit of 0.85 GW/cm <sup>2</sup> or a 5A/700ÅV Handling Capabilities. IEEE Transactions on Power Electronics, 2021, 36, 6179-6182.	5.4	88
5	A Review of THz Modulators with Dynamic Tunable Metasurfaces. Nanomaterials, 2019, 9, 965.	1.9	86
6	A Novel 220-GHz GaN Diode On-Chip Tripler With High Driven Power. IEEE Electron Device Letters, 2019, 40, 780-783.	2.2	85
7	Large phase modulation of THz wave via an enhanced resonant active HEMT metasurface. Nanophotonics, 2018, 8, 153-170.	2.9	75
8	2.41 kV Vertical P-NiO/n-Ga <sub>2</sub> O <sub>3</sub> Heterojunction Diodes With a Record Baliga's Figure-of-Merit of 5.18 GW/cm <sup>2</sup> . IEEE Transactions on Power Electronics, 2022, 37, 3743-3746.	5.4	72
9	High-Speed Efficient Terahertz Modulation Based on Tunable Collective-Individual State Conversion within an Active 3 nm Two-Dimensional Electron Gas Metasurface. Nano Letters, 2019, 19, 7588-7597.	4.5	64
10	High-precision digital terahertz phase manipulation within a multichannel field perturbation coding chip. Nature Photonics, 2021, 15, 751-757.	15.6	54
11	High-Voltage ( $\overline{\text{ext}}\{2\}$ 01\$ ) $\text{Ga}_{2\text{O}_3}$ Vertical Schottky Barrier Diode With Thermally-Oxidized Termination. IEEE Electron Device Letters, 2020, 41, 131-134.	2.2	52
12	A 177-183 GHz High-Power GaN-Based Frequency Doubler With Over 200 mW Output Power. IEEE Electron Device Letters, 2020, 41, 669-672.	2.2	39
13	GaN planar Schottky barrier diode with cutoff frequency of 902 GHz. Electronics Letters, 2016, 52, 1408-1410.	0.5	27
14	Large-Area 4H-SiC Ultraviolet Avalanche Photodiodes Based on Variable-Temperature Reflow Technique. IEEE Electron Device Letters, 2018, 39, 1724-1727.	2.2	21
15	High-Power 300 GHz Solid-State Source Chain Based on GaN Doublers. IEEE Electron Device Letters, 2021, 42, 1588-1591.	2.2	15
16	GaN-Based Frequency Doubler With Pulsed Output Power Over 1 W at 216 GHz. IEEE Electron Device Letters, 2021, 42, 1739-1742.	2.2	7
17	A Review of Terahertz Sources Based on Planar Schottky Diodes. Chinese Journal of Electronics, 2022, 31, 467-487.	0.7	3
18	Terahertz Frequency Quadrupler Based on a $2\text{Å}^{-2}$ Single-chip GaAs Monolithic Integration. , 2021, , .		1